

**Silicon PNP transistor epitaxial type
AP020**

[Applications]

High voltage driver

[Feature]

High voltage VCEO= VCBO= -300V

[Absolute maximum ratings (Ta=25C)]

| Characteristic | Symbol | Maximum ratings | Unit |
|---------------------------|--------|-----------------|------|
| Collector-base voltage | VCBO | -300 | V |
| Collector-emitter voltage | VCEO | -300 | V |
| Emitter-base voltage | VEBO | -7 | V |
| Collector current | IC | -100 | mA |
| Junction temperature | Tj | 150 | C |
| Storage temperature | Tstg | -55 to 150 | C |

[Electrical characteristics (Ta=25C)]

| Characteristic | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|----------|------|------|------|------|----------------------------|
| Collector-base breakdown voltage | BVCBO | -300 | - | - | V | IC= -50uA, IE= 0A |
| Collector-emitter breakdown voltage | BVCEO | -300 | - | - | V | IC= -10mA, IB= 0A |
| Emitter-base breakdown voltage | BVEBO | -7 | - | - | V | IE= -50uA, IC= 0A |
| Collector-cut off current | ICBO | - | - | -500 | nA | VCB= -300V, IE= 0A |
| DC current gain | hFE | 60 | - | 280 | - | VCE= -10V, IC= -10mA |
| Collector-emitter saturation voltage | VCE(sat) | - | - | -0.5 | V | IC= -100mA, IB= -10mA |
| Transition frequency | fT | - | 65 | - | MHz | VCE= -10V, IE= 10mA |
| Collector output capacitance | Cob | - | 4.5 | - | pF | VCB= -20V, f= 1MHz, IE= 0A |

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.